

PTB 20017

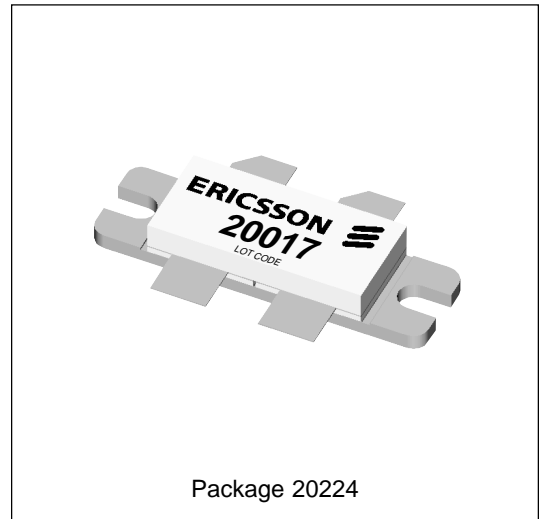
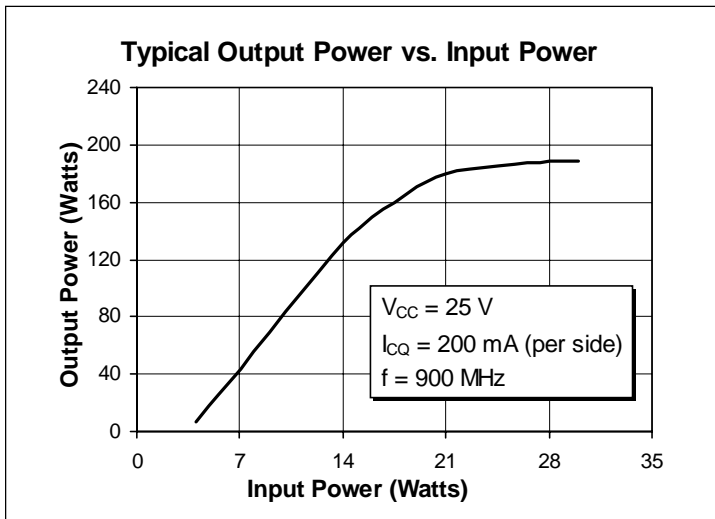
150 Watts, 860–900 MHz

Cellular Radio RF Power Transistor

Description

The 20017 is a class AB, NPN, common emitter RF power transistor intended for 25 Vdc operation across the 860 to 900 MHz cellular radio frequency band. Rated at 150 watts minimum output power, it may be used for both CW and PEP applications. Ion implantation, nitride surface passivation and gold metallization are used to ensure excellent device reliability. 100% lot traceability is standard.

- 150 Watts, 860–900 MHz
- Class AB Characteristics
- 50% Collector Efficiency at 150 Watts
- Gold Metallization
- Silicon Nitride Passivated



Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CER}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage (collector open)	V_{EBO}	4.0	Vdc
Collector Current (continuous)	I_C	25	Adc
Total Device Dissipation at $T_{flange} = 25^{\circ}C$ Above $25^{\circ}C$ derate by	P_D	330 1.89	Watts W/ $^{\circ}C$
Storage Temperature Range	T_{STG}	-40 to +150	$^{\circ}C$
Thermal Resistance ($T_{flange} = 70^{\circ}C$)	$R_{\theta JC}$	0.53	$^{\circ}C/W$

Electrical Characteristics (100% Tested)

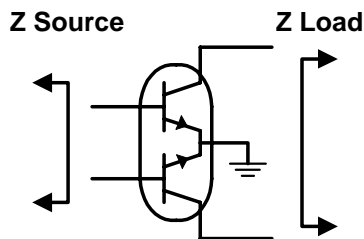
Characteristic	Conditions	Symbol	Min	Typ	Max	Units
Breakdown Voltage C to E	$I_B = 0\text{ A}, I_C = 100\text{ mA}$	$V_{(BR)CEO}$	25	30	—	Volts
Breakdown Voltage C to E	$V_{BE} = 0\text{ V}, I_C = 100\text{ mA}$	$V_{(BR)CES}$	55	70	—	Volts
Breakdown Voltage E to B	$I_C = 0\text{ A}, I_E = 5\text{ mA}$	$V_{(BR)EBO}$	3.5	5	—	Volts
DC Current Gain	$V_{CE} = 5\text{ V}, I_C = 1\text{ A}$	h_{FE}	20	50	100	—

RF Specifications (100% Tested)

Characteristic	Symbol	Min	Typ	Max	Units
Gain ($V_{CC} = 25\text{ Vdc}, P_{Out} = 150\text{ W}, I_{CQ} = 200\text{ mA}$ per side, $f = 900\text{ MHz}$)	G_{pe}	8.0	9.0	—	dB
Collector Efficiency ($V_{CC} = 25\text{ Vdc}, P_{Out} = 150\text{ W}, I_{CQ} = 200\text{ mA}$ per side, $f = 900\text{ MHz}$)	η_C	50	—	—	%
Intermodulation Distortion ($V_{CC} = 25\text{ Vdc}, P_{Out} = 150\text{ W(PEP)}, I_{CQ} = 200\text{ mA}$ per side, $f_1 = 899\text{ MHz}, f_2 = 900\text{ MHz}$)	IMD	—	-28	—	dBc
Load Mismatch Tolerance ($V_{CC} = 25\text{ Vdc}, P_{Out} = 150\text{ W(PEP)}, I_{CQ} = 200\text{ mA}$ per side $f = 900\text{ MHz}$ —all phase angles at frequency of test)	Ψ	—	—	5:1	—

Impedance Data (data shown for fixed-tuned broadband circuit)

($V_{CC} = 25\text{ Vdc}, P_{Out} = 150\text{ W}, I_{CQ} = 200\text{ mA}$ per side)



Frequency MHz	Z Source		Z Load	
	R	jX	R	jX
860	3.4	-6.7	3.5	-3.1
880	3.1	-6.1	3.4	-2.6
900	2.9	-5.6	3.2	-2.1

